

Silicon NPN Power Transistors

2SC2565

DESCRIPTION

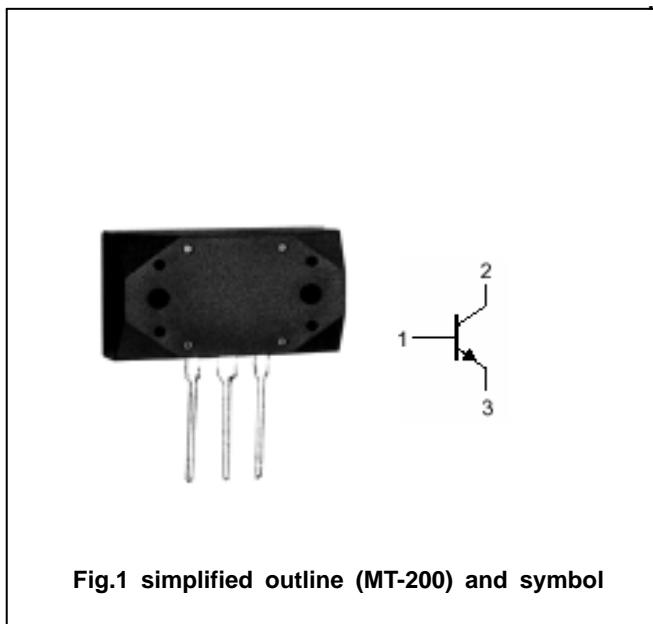
- With MT-200 package
- Complement to type 2SA1095
- High transition frequency

APPLICATIONS

- For power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	160	V
V _{CEO}	Collector-emitter voltage	Open base	160	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		15	A
I _B	Base current		1.5	A
P _C	Collector power dissipation	T _C =25	150	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =0.1A; I _B =0	160			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5 A; I _B =0.5 A			2.0	V
V _{BE}	Base-emitter on voltage	I _C =5A ; V _{CE} =5V			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =160V; I _E =0			50	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			50	μ A
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	55		240	
h _{FE-2}	DC current gain	I _C =5A ; V _{CE} =5V	40			
f _T	Transition frequency	I _C =1A ; V _{CE} =10V		80		MHz
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V;f=1MHz		200		pF

◆ h_{FE-1} classifications

R	O	Y
55-110	80-160	120-240

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PACKAGE OUTLINE

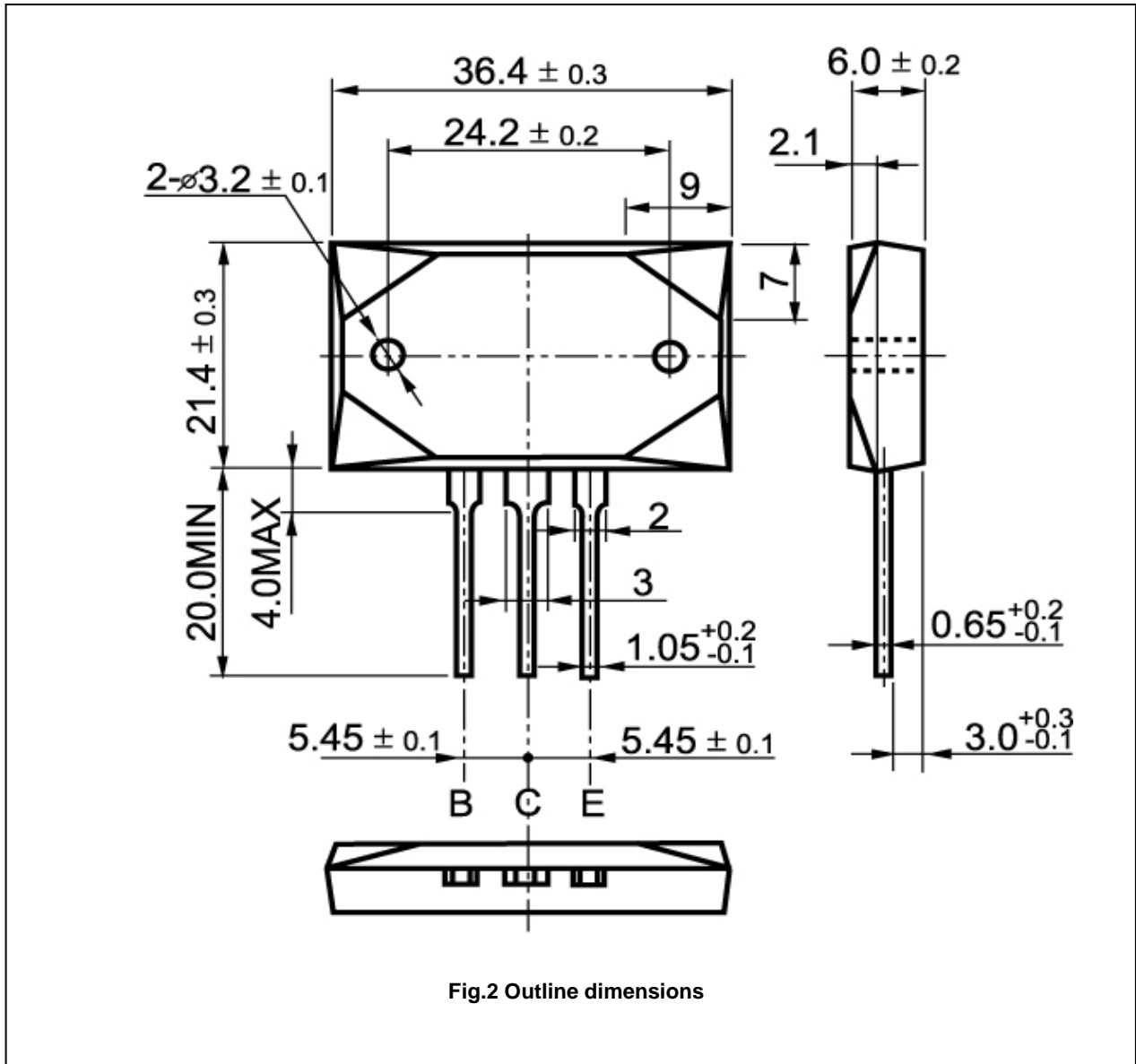


Fig.2 Outline dimensions